Notice of Allowability	Application No.  09/964,463 Examiner  Quyen P. Leung	Applicant(s)  ONOMURA ET AL.  Art Unit  2828
Notice of Allowability	Examiner  Quyen P. Leung	Art Unit
Notice of Allowability	Quyen P. Leung	
		2828
	pears on the cover sheet wit	2020
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS !! herewith (or previously mailed), a Notice of Allowance (PTOL-8! NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT! of the Office or upon petition by the applicant. See 37 CFR 1.3	S (OR REMAINS) CLOSED in 5) or other appropriate commu RIGHTS. This application is s	this application. If not included inication will be mailed in due course. <b>THIS</b>
1. This communication is responsive to 11/15/2004.		
2. 🛮 The allowed claim(s) is/are <u>1, 5, 7, 9-12, 14-17, 21, 23, 2</u>	<u>24, 26, 28-33</u> .	
3. 🛮 The drawings filed on <u>28 September 2001</u> are accepted I	by the Examiner.	
4.  Acknowledgment is made of a claim for foreign priority of a)  All b)  Some* c)  None of the:  1.  Certified copies of the priority documents have 2.  Certified copies of the priority documents have 3.  Copies of the certified copies of the priority of International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE noted below. Failure to timely comply will result in ABANDON THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  5.  A SUBSTITUTE OATH OR DECLARATION must be subsined in the su	ve been received. ve been received in Application documents have been received and application documents have been received and application to file IMENT of this application.  mitted. Note the attached EXA eves reason(s) why the oath or just be submitted.  erson's Patent Drawing Review —  er's Amendment / Comment or at 1.84(c)) should be written on the the header according to 37 CF and the property of the prope	n No  If in this national stage application from the a reply complying with the requirements  AMINER'S AMENDMENT or NOTICE OF declaration is deficient.  If (PTO-948) attached  in the Office action of the drawings in the front (not the back) of R 1.121(d).  ERIAL must be submitted. Note the
Attachment(s)  1. ☐ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB. Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	) 6. ☐ Interview Su Paper No./l /08), 7. ☐ Examiner's	formal Patent Application (PTO-152)  Immary (PTO-413),  Mail Date  Amendment/Comment  Statement of Reasons for Allowance
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## **REASONS FOR ALLOWANCE**

- 1. In response to applicant's amendment after final filed 11/15/2004 claims 2-4, 6, 8, 13, 18-20, 22, 25 and 27 have been canceled; claims 1, 11, 21, 24, 26, amended; and claims 32-33 added. Claims 1, 5, 7, 9-12, 14-17, 21, 23, 24, 26, 28-33 are pending and allowed.
- 2. The following is an examiner's statement of reasons for allowance: The claims are allowed mainly because the cited prior art do not teach or fairly suggest a semiconductor laser diode comprising the combination of a first conductive type AlxGa1-xN layer (0.04 <=x <= 0.08) having a thickness of 0.3 to 1.0 microns and a first conductive type AlyGa1-yN (0.05 <=y<=0.20, x<y), as in independent claim 1; or the combination of a first conductive type AlxGa1-xN layer (0.04 <=x <= 0.08) having a thickness of 0.3 to 1.0 microns, the n-type superlattice clad and the p-type superlattice clad, as in independent claim 21; or the combination of a first conductive type AlxGa1xN layer (0.04 <=x <= 0.08) having a thickness of 0.3 to 1.0 microns and the first conductive type GaN substrate, as in independent claim 24; or the combination of a first conductive type AlxGa1-xN layer (0.04 <=x <= 0.08) having a thickness of 0.3 to 1.0 microns and the first conductive type clad layer having a superlattice structure in which AlyGa1-yN (0.05<=y<=0.20, x<y) and GaN are alternately laminated, as in independent claim 32; or the combination of a first conductive type AlxGa1-xN layer (0.04 <=x <= 0.08) having a thickness of 0.3 to 1.0 microns and the first conductive type clad layer has higher average composition of Al than the first conductive type nitride semiconductor layer, as in independent claim 33.

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Quyen P. Leung whose telephone number is (571)272-1943. The examiner can normally be reached on 8-4:30, M-F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Minsun Harvey can be reached on (571)272-1835. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Quyen P. Leung Primary Examiner Art Unit 2828

**QPL**